Features
- Single Biasing Voltage (Self Biased)
- Frequency: 4-8GHz
- Small Signal Gain: 27dB
- Noise Figure: 0.7dB typ./0.8dB max.
- P1dB: 12dBm
- Power supply: +5V/30mA
- Input/Output: 50Ω
- Die Size: 1.75 x 1.25 x 0.09 mm

Typical Applications
- Test Instrumentation
- Microwave Radio & VSAT
- Military & Space
- Telecom Infrastructure
- Fiber Optics

Electrical Specifications
TA = +25°C, Vd = +5V

<table>
<thead>
<tr>
<th>Parameters</th>
<th>Min.</th>
<th>Typ.</th>
<th>Max.</th>
<th>Units</th>
</tr>
</thead>
<tbody>
<tr>
<td>Frequency</td>
<td>4-8</td>
<td></td>
<td></td>
<td>GHz</td>
</tr>
<tr>
<td>Small Signal Gain</td>
<td>-</td>
<td>27</td>
<td>27.5</td>
<td>dB</td>
</tr>
<tr>
<td>Gain Flatness</td>
<td>±0.25</td>
<td></td>
<td></td>
<td>dB</td>
</tr>
<tr>
<td>Noise Figure</td>
<td>-</td>
<td>0.7</td>
<td>0.8</td>
<td>dB</td>
</tr>
<tr>
<td>Output 1dB Compression (P1dB)</td>
<td>11.5</td>
<td>12</td>
<td>13</td>
<td>dBm</td>
</tr>
<tr>
<td>Saturated Output Power (Psat)</td>
<td>12.5</td>
<td>13</td>
<td>14.5</td>
<td>dBm</td>
</tr>
<tr>
<td>Input Return Loss</td>
<td>12</td>
<td>20</td>
<td>-</td>
<td>dB</td>
</tr>
<tr>
<td>Output Return Loss</td>
<td>16</td>
<td>20</td>
<td>-</td>
<td>dB</td>
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<tr>
<td>Static current</td>
<td>30</td>
<td></td>
<td></td>
<td>mA</td>
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</tbody>
</table>
GaAs MMIC
Low Noise Amplifier
4-8GHz

Gain vs. Frequency
- Small Signal Gain (dB)
- Frequency (GHz)

Noise Figure vs. Frequency
- Noise Figure (dB)
- Frequency (GHz)

Input Return Loss vs. Frequency
- S11 (dB)
- Frequency (GHz)

Output Return Loss vs. Frequency
- S22 (dB)
- Frequency (GHz)

Reverse Isolation vs. Frequency
- S12 (dB)
- Frequency (GHz)

P1dB vs. Frequency
- P1dB (dBm)
- Frequency (GHz)
### Pad Description

<table>
<thead>
<tr>
<th>Pad</th>
<th>Function</th>
<th>Description</th>
<th>Equivalent Circuit</th>
</tr>
</thead>
<tbody>
<tr>
<td>1</td>
<td>RF IN</td>
<td>RF signal input terminal, no blocking capacitor required.</td>
<td><img src="image" alt="RF IN Circuit" /></td>
</tr>
<tr>
<td>2</td>
<td>RF OUT</td>
<td>RF signal output terminal, no blocking capacitor required.</td>
<td><img src="image" alt="RF OUT Circuit" /></td>
</tr>
<tr>
<td>3</td>
<td>VDD</td>
<td>Amplifier drain bias; external 100pF bypass capacitor required.</td>
<td><img src="image" alt="VDD Circuit" /></td>
</tr>
<tr>
<td>Die bottom</td>
<td>GND</td>
<td>Die bottom must be connected to RF/DC ground.</td>
<td><img src="image" alt="GND Circuit" /></td>
</tr>
</tbody>
</table>
Assembly Drawing

Notes:
1. Die thickness: 100um
2. Typical bond pad is 100*100 μm²
3. Bond pad metalization: Gold
4. Backside metalization: Gold
5. Backside of the die (GND)
6. No connection required for unlabeled bond pads

Maximum Ratings:
1. Maximum drain voltage: +7V
2. Maximum input power: +20dBm
3. Operating temperature: -55°C to +85°C
4. Storage temperature: -65°C to +150°C